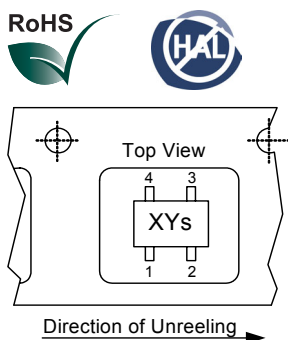
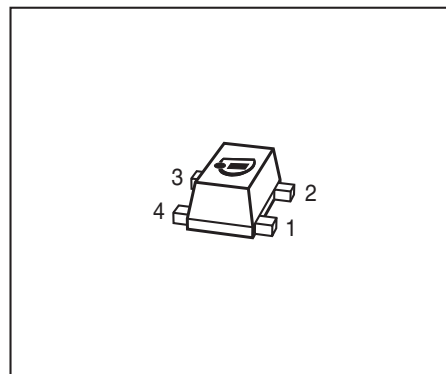


Linear Low Noise SiGe:C Bipolar RF Transistor

- For medium power amplifiers and driver stages
- Based on Infineon' s reliable high volume Silicon Germanium technology
- High $OIP3$ and P_{-1dB}
- Ideal for low phase noise oscillators
- Maxim. available Gain $G_{ma} = 21.5$ dB at 1.8 GHz
Minimun noise figure $NF_{min} = 0.8$ dB at 1.8 GHz
- Pb-free (RoHS compliant) and halogen-free thin small flat package with visible leads
- Qualification report according to AEC-Q101 available



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP650F	R5s	1=B	2=E	3=C	4=E	-	-	TSFP-4

Maximum Ratings at $T_A = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage $T_A = 25\text{ °C}$ $T_A = -55\text{ °C}$	V_{CEO}	4 3.7	V
Collector-emitter voltage	V_{CES}	13	
Collector-base voltage	V_{CBO}	13	
Emitter-base voltage	V_{EBO}	1.2	
Collector current	I_C	150	mA
Base current	I_B	10	
Total power dissipation ¹⁾ $T_S \leq 85\text{ °C}$	P_{tot}	500	mW
Junction temperature	T_J	150	°C
Storage temperature	T_{Stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}	130	K/W

Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Collector-emitter breakdown voltage $I_C = 3\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	4	4.5	-	V
Collector-emitter cutoff current $V_{CE} = 13\text{ V}$, $V_{BE} = 0$	I_{CES}	-	-	100	µA
Collector-base cutoff current $V_{CB} = 5\text{ V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 0.5\text{ V}$, $I_C = 0$	I_{EBO}	-	-	10	µA
DC current gain $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, pulse measured	h_{FE}	110	180	270	-

¹⁾ T_S is measured on the emitter lead at the soldering point to the pcb

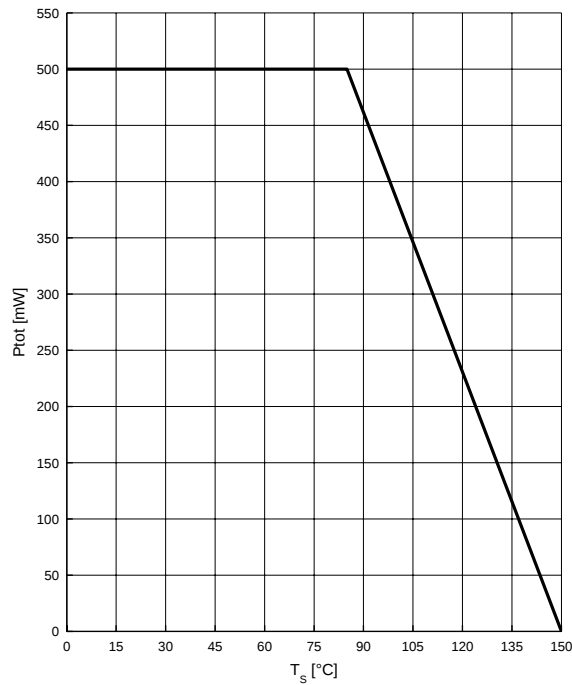
²⁾ For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

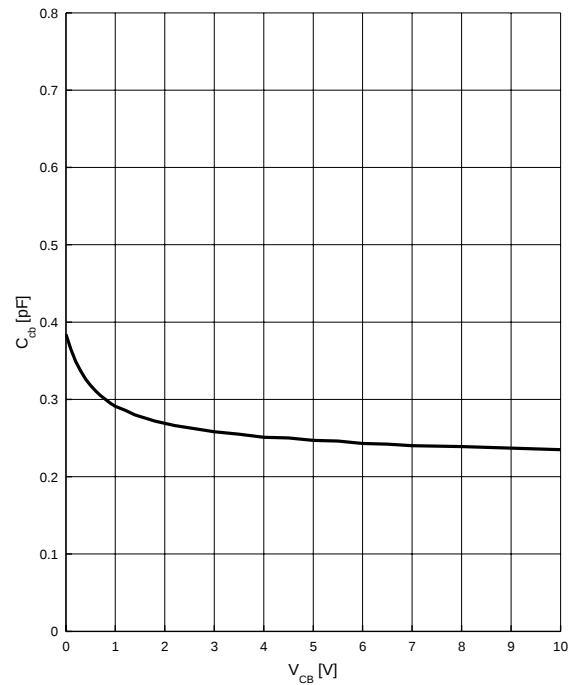
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 1\text{ GHz}$	f_T	-	42	-	GHz
Collector-base capacitance $V_{CB} = 3\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.26	-	pF
Collector emitter capacitance $V_{CE} = 3\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.45	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	1.3	-	
Minimum noise figure $I_C = 10\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$ $I_C = 10\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 6\text{ GHz}$, $Z_S = Z_{Sopt}$	NF_{min}	- -	0.8 1.9	- -	dB
Power gain, maximum available ¹⁾ $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$ $f = 6\text{ GHz}$	G_{ma}	- -	21.5 11	- -	
Transducer gain $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 1.8\text{ GHz}$ $f = 6\text{ GHz}$	$ S_{21e} ^2$	15 -	17.5 7.5	- -	
Third order intercept point at output ²⁾ $V_{CE} = 3\text{ V}$, $I_C = 80\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\text{ }\Omega$	$IP3$	-	31	-	dBm
1dB compression point at output $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 1.8\text{ GHz}$	P_{-1dB}	-	17.5	-	

¹⁾ $G_{ma} = |S_{21e}| / |S_{12e}| (k - (k^2 - 1)^{1/2})$
²⁾ $IP3$ value depends on termination of all intermodulation frequency components.
Termination used for this measurement is $50\text{ }\Omega$ from 0.1 MHz to 6 GHz

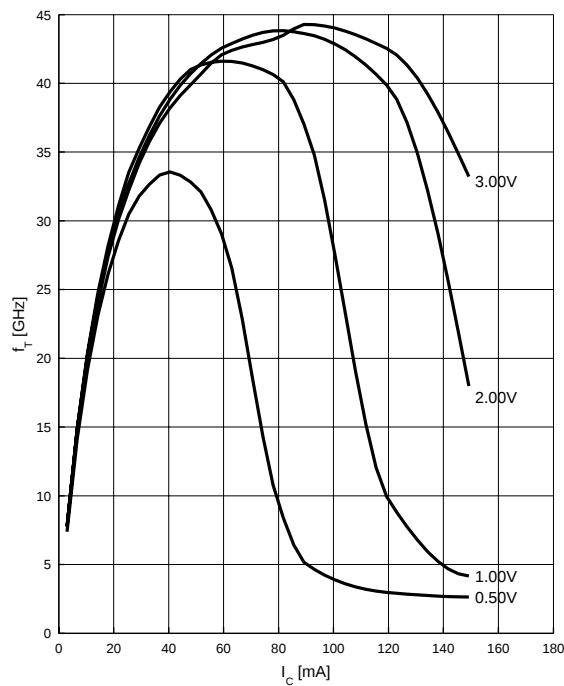
Total power dissipation $P_{\text{tot}} = f(T_S)$



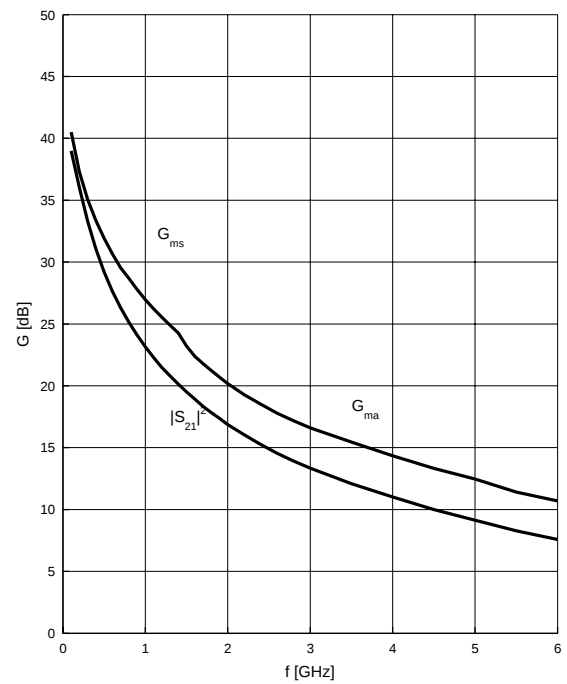
Collector-base capacitance $C_{\text{cb}} = f(V_{\text{CB}})$
 $f = 1 \text{ MHz}$



Transition frequency $f_T = f(I_C)$
 $V_{\text{CE}} = \text{parameter in V, } f = 1 \text{ GHz}$



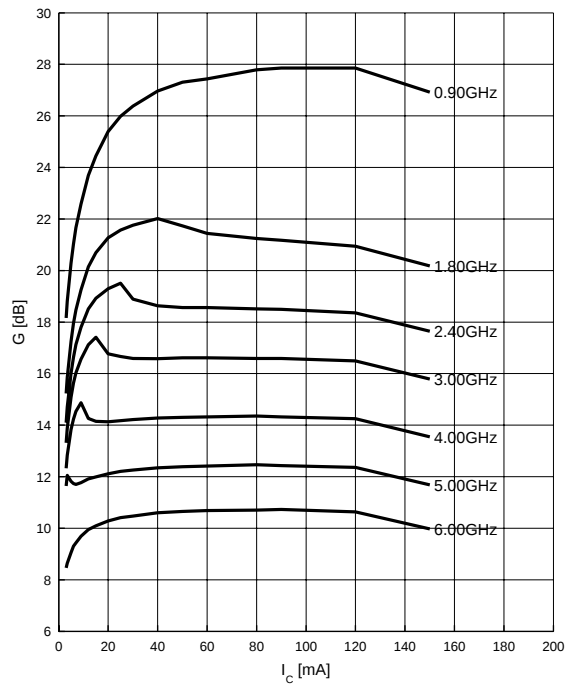
Power gain $G_{\text{ma}}, G_{\text{ms}} = f(f)$
 $V_{\text{CE}} = 3 \text{ V, } I_C = 80 \text{ mA}$



Power gain G_{ma} , $G_{ms} = f(I_C)$

$V_{CE} = 3 \text{ V}$

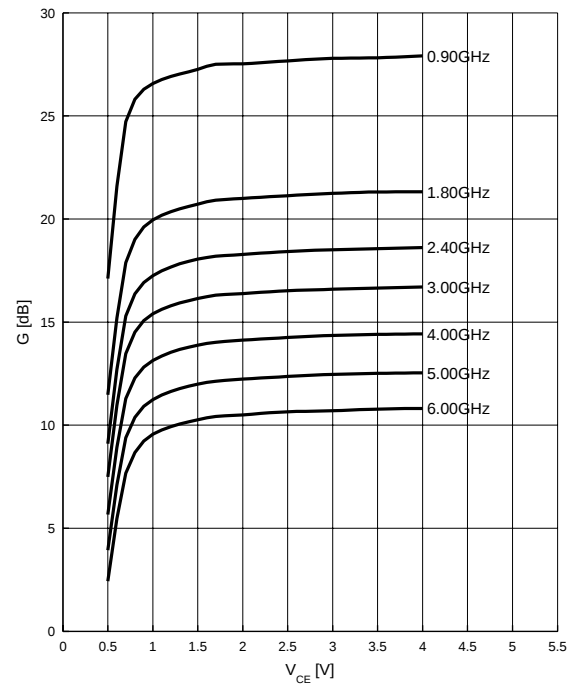
$f = \text{parameter in GHz}$

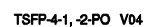


Power gain G_{ma} , $G_{ms} = f(V_{CE})$

$I_C = 80 \text{ mA}$

$f = \text{parameter in GHz}$

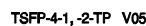




TSFP-4-1, -2-FP V04

The diagram shows a rectangular component with four pins. Labels with leader lines point to specific parts: 'Manufacturer' points to the Infineon logo at the top right; 'Pin' points to the bottom-left pin; 'Marking' points to the text 'XY S' inside the component's frame.

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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